

2inch Cplane Patterned Sapphire Substrate (PSS



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Patterned Sapphire Substrates (PSS) is micro-patterned sapphire substrate used to for GaN based light emitting diodes(LEDS). The PSS reduces the dislocation density in the GaN layer, enhances the light extraction efficiency and increase LEDs'brightness.

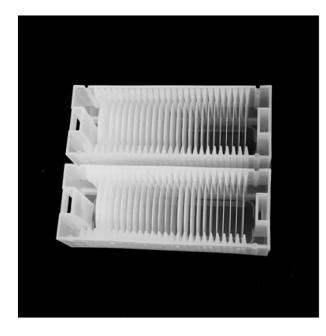
2inch Cplane Patterned Sapphire Substrate (PSS) Detailed specification:

Crystal Material	99.996%,high purity, monocrystalline Al2O3
Grade	Prime
Orientation	Cplane to Mplane
Diameter	2 inch
Patterned Spec	Diameter: 2.7 \pm 0.15 $\mu m;$ Spacing: 0.3 \pm 0.15 $\mu m;$ Depth: 1.75 \pm 0.15 μm
Pattern type	3µm pitch, Cone Type
Thickness	430±15 µm
Surface	SSP or DSP
TTV/BOW/WARP	≤ 10 μm
Package	Class 100 clean room cleaning, vacuum packaging; 25 pieces in one cassette packaging or individual packaging

Aplane, Mplane, Rplane Sapphire Substrate

• Aplane, Mplane, Rplane Sapphire Substrate

• The material is grown and orientated, and substrates are fabricated and polished to an extremely smooth damage free Epi-Ready surface on one or both sides of the wafer. A variety of wafer orientations (Cplane, Mplane, Aplane, Rplane) and sizes up to 8"(2inch to 8inch) diameter are available.



Crystal Materials	99,996%, High Purity, Monocrys			talline Al ₂ O ₃	
Diameter	50.8 mm ± 0.1 mm				
Thickness	430 μm ± 25 μm				
Orientation	A-plane (11-20) ± 0.2°	M-Plane (1-100) ± 0.2°		R-Plane (1-102) ± 0.2°	
Primary flat Orientation	C-plane (0001) ± 0.2°	A-plane (11-20) ± 0.2°		Cplane projection to R-plane CCW 45 ± 1°	
Primary flat length	16.0 mm ± 1.0 mm				
Front Surface	Epi-polished, Ra < 0.3 nm (by AFM)				
Back Surface	Fine ground, Ra = 0.5 m(SSP)	μm to 1.2 μ	Epi-polis	hed, Ra < 0.2 nm (by AFM) (DSP)	
TTV	< 8 µm				
LTV	<8 µm				
BOW	< 8 µm				
Cleaning/ packaging	Class 100 clean room cleaning no scratch,dig and crack and vacuum packagir derived nitrogen, 25 pieces in one cassette packaging				

Crystal Material	99,996% of Al2O3, High Purity, Monocrystalline, Al2O3				
Crystal quality	Inclusions, block marks, twins, Color, micro-bubbles and dispers centers are non-existent				
D: 1	2 inch	4 inch	6 inch		
Diameter	50.8± 0.1mm	100±0.2mm	150.0±0.2 mm		
Thickness	430±25µm	650±20µm	1200±25µm		
Orientation	C- plane (0001) to M-plane (1-100) 0.2°±0.1°				
Primary flat Orientation	A-plane (1 1-2 0) ± 0.2°				
Primary flat length	16.0±1.0mm	32.0±1.0 mm	50±1.0 mm		
TTV	≤10µm	≤20µm	≤25µm		
LTV	≤10µm	≤20µm	≤25µm		
BOW	≤10µm	≤20µm	≤25µm		
WARP	≤10µm	≤20µm	≤25µm		
Front Surface	Epi-Polished (Ra< 0.2nm)				
Back Surface	Fine ground (Ra=0.5 to 1.2 µm), Epi-Polished (Ra< 0.2nm)				
Cleaning/packaging	Class 100 clean room cleaning, vacuum packaging derived nitroger				
Note	Sapphire substrates of all kinds of specifications are available according to your specific requirement				

Detailed specification:



2inch To 8inch Sapphire Substrate

Sapphire Substrate is a kind of widely used single crystal substrate material. It is the first choice substrate in the current blue, violet, white light-emitting diode (LED) and blue laser (LD) industry (gallium nitride film needs to be epitaxial on the sapphire substrate first), and it is also an important superconducting film substrate.

2~12 Inch CZ Silicon Wafers

Silicon wafer is an important material for making integrated circuits. Various semiconductor devices can be made through photolithography and ion implantation of silicon wafers.

silicon wafers have been widely used in aerospace, industry, agriculture and national defense, and even sneaked into every family.

Products Description Products Specifications:					
Growth Method	CZ				
Type(doping)	P-type (8 doped) or Ntype (P doped)				
Orientation	(100) or (111)				
Diameter	2inch~12inch				
Thickness	200-1500 µm,				
Surface	SSP or DSP				
TTV&BOW	'≤15 pm				
Resistivity	0+300ohm.cm				
Cleaning/ packaging	Vacuum packaging, 25 pieces in one cassette packaging				
Stock situation	your required specification can be sent to us for checking				

